Preferred Device

Small Signal MOSFET 200 mAmps, 60 Volts

N-Channel TO-92

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	60	Vdc
Drain–Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V_{DGR}	60	Vdc
Gate–Source Voltage – Continuous – Non–repetitive ($t_p \le 50 \mu s$)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current - Continuous - Pulsed	I _D	200 500	mAdc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	357	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	T _L	300	°C

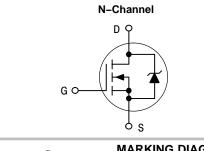


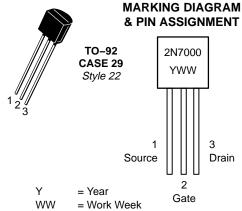
ON Semiconductor®

http://onsemi.com

200 mAMPS 60 VOLTS

 $R_{DS(on)} = 5 \Omega$





ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit	
OFF CHARACTERISTICS						
Drain–Source Breakdown Voltage (V _{GS} = 0, I _D = 10 μAdc)		V _{(BR)DSS}	60	_	Vdc	
Zero Gate Voltage Drain Current $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0)$ $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0, T_{J} = 125^{\circ}\text{C})$		I _{DSS}	_ _ _	1.0 1.0	μAdc mAdc	
Gate–Body Leakage Current, Forward (V _{GSF} = 15 Vdc, V _{DS} = 0)		I _{GSSF}	_	-10	nAdc	
ON CHARACTERISTICS (N	lote 1)					
Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.0 mAdc)	V _{GS(th)}	0.8	3.0	Vdc		
Static Drain–Source On–Resis $(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAc})$	r _{DS(on)}	- -	5.0 6.0	Ohm		
Drain–Source On–Voltage $(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc})$		V _{DS(on)}	_ _	2.5 0.45	Vdc	
On–State Drain Current (V _{GS} = 4.5 Vdc, V _{DS} = 10 Vdc)		I _{d(on)}	75	-	mAdc	
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 200 mAdc)		9fs	100	-	μmhos	
DYNAMIC CHARACTERIST	rics			-	-!	
Input Capacitance		C _{iss}	_	60	pF	
Output Capacitance	$(V_{DS} = 25 \text{ V}, V_{GS} = 0,$	C _{oss}	-	25		
Reverse Transfer Capacitance	f = 1.0 MHz)	C _{rss}	_	5.0		
SWITCHING CHARACTER	ISTICS (Note 1)			•	•	
Turn-On Delay Time	(V _{DD} = 15 V, I _D = 500 mA,	t _{on}	_	10	ns	
Turn-Off Delay Time	$R_G = 25 \Omega$, $R_L = 30 \Omega$, $V_{gen} = 10 V$)	t _{off}	-	10	1	

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

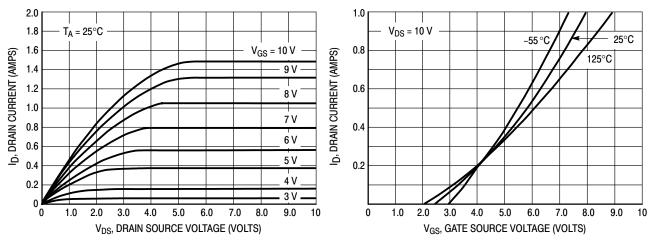


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics

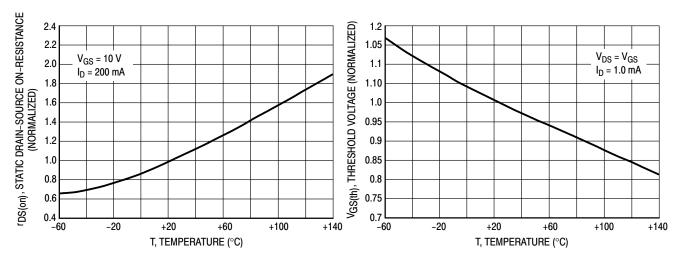


Figure 3. Temperature versus Static Drain-Source On-Resistance

Figure 4. Temperature versus Gate Threshold Voltage

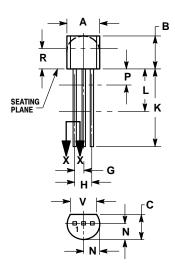
ORDERING INFORMATION

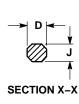
Device	Package	Shipping [†]	
2N7000	TO-92	1000 Unit/Box	
2N7000G	TO-92 (Pb-Free)	1000 Unit/Box	
2N7000RLRA	TO-92	2000 Tape & Reel	
2N7000RLRAG	TO-92 (Pb-Free)	2000 Tape & Reel	
2N7000RLRM	TO-92	2000 Ammo Pack	
2N7000RLRMG	TO-92 (Pb-Free)	2000 Ammo Pack	
2N7000RLRP	TO-92	2000 Ammo Pack	
2N7000RLRPG	TO-92 (Pb-Free)	2000 Ammo Pack	
2N7000ZL1	TO-92	2000 Ammo Pack	
2N7000ZL1G	TO-92 (Pb-Free)	2000 Ammo Pack	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 CASE 29-11 **ISSUE AL**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

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